74HC4538-Q100; 74HCT4538-Q100

Dual retriggerable precision monostable multivibrator

Rev. 1 — 2 August 2012 Product data sheet

1. General description

The 74HC4538-Q100; 74HCT4538-Q100 are high-speed Si-gate CMOS devices and are pin compatible with Low-power Schottky TTL (LSTTL). They are specified in compliance with JEDEC standard no. 7A.

The 74HC4538-Q100; 74HCT4538-Q100 are dual retriggerable-resettable monostable multivibrators. Each multivibrator has:

- an active LOW trigger/retrigger input ($n\overline{A}$)
- an active HIGH trigger/retrigger input (nB)
- an overriding active LOW direct reset input ($n\overline{CD}$)
- an output (nQ) and its complement ($n\overline{Q}$)
- two pins (nREXT/CEXT and nCEXT) for connecting the external timing components C_{EXT} and R_{EXT}

Typical pulse width variation over the specified temperature range is ±0.2 %.

The multivibrator may be triggered by either the positive or the negative edges of the input pulse. The duration and accuracy of the output pulse are determined by the external timing components C_{EXT} and R_{EXT}. The output pulse width (t_W) is equal to $0.7 \times R_{EXT} \times C_{EXT}$. The linear design techniques guarantee precise control of the output pulse width. A LOW level at $n\overline{CD}$ terminates the output pulse immediately. Schmitt trigger action on pins $n\overline{A}$ and nB makes the circuit highly tolerant of slower rise and fall times.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from −40 °C to +85 °C and from −40 °C to +125 °C
- Tolerant of slow trigger rise and fall times
- Separate reset inputs
- Triggering from falling or rising edge
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC4538D-Q100	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT4538D-Q100				
74HC4538PW-Q100	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HCT4538PW-Q100				

4. Functional diagram

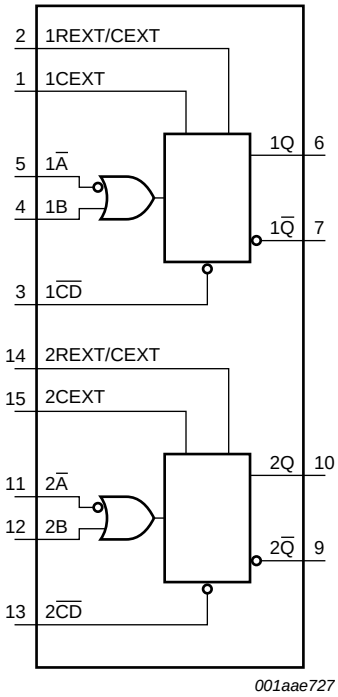


Fig 1. Functional diagram

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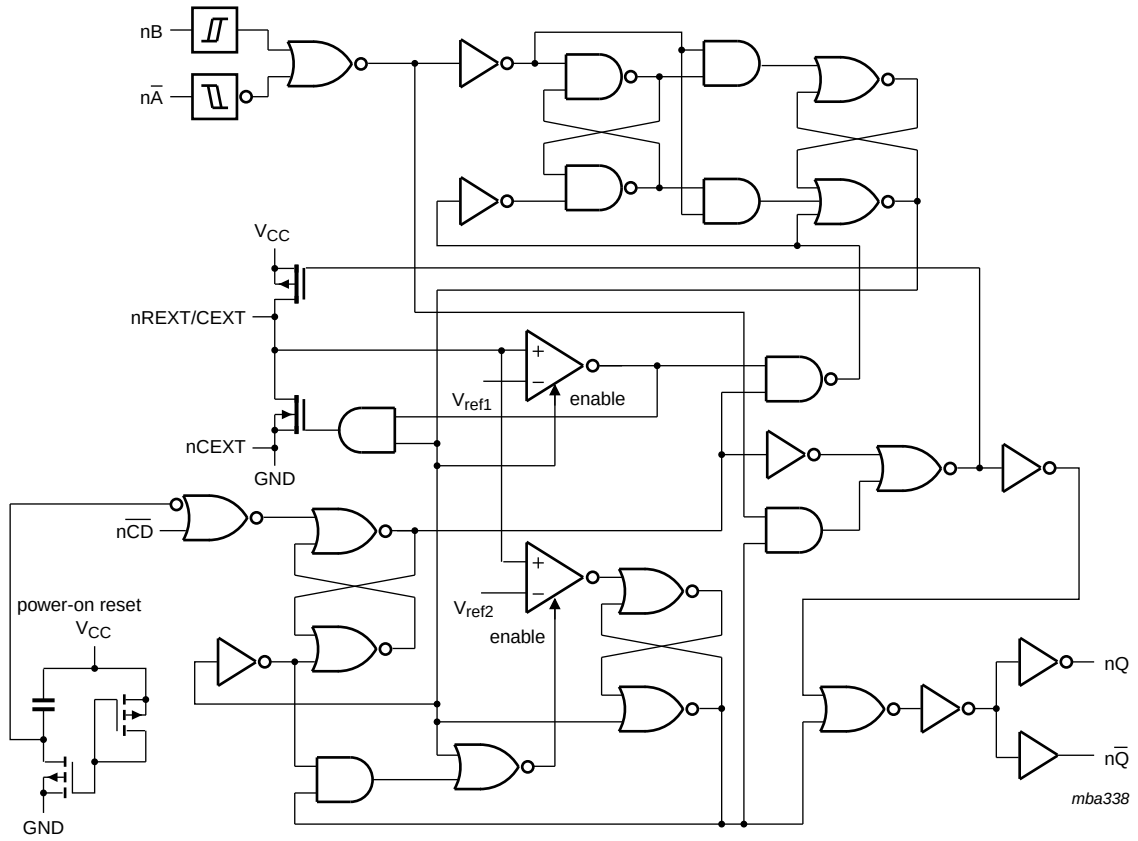


Fig 2. Logic diagram (one multivibrator)

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5. Pinning information

5.1 Pinning

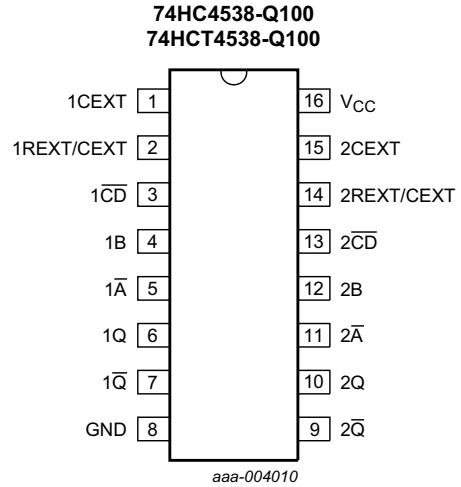


Fig 3. Pin configuration for SO16

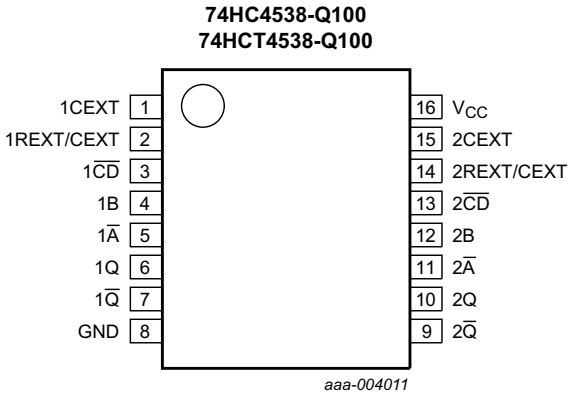


Fig 4. Pin configuration for TSSOP16

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1CEXT, 2CEXT	1, 15	external capacitor connection (always connected to ground)
1REXT/CEXT, 2REXT/CEXT	2, 14	external capacitor/resistor connection
$1\overline{CD}$, $2\overline{CD}$	3, 13	direct reset input (active LOW)
1B, 2B	4, 12	input (LOW to HIGH triggered)
$1\overline{A}$, $2\overline{A}$	5, 11	input (HIGH to LOW triggered)
1Q, 2Q	6, 10	output
$1\overline{Q}$, $2\overline{Q}$	7, 9	complementary output (active LOW)
GND	8	ground (0 V)
V_{CC}	16	supply voltage

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6. Functional description

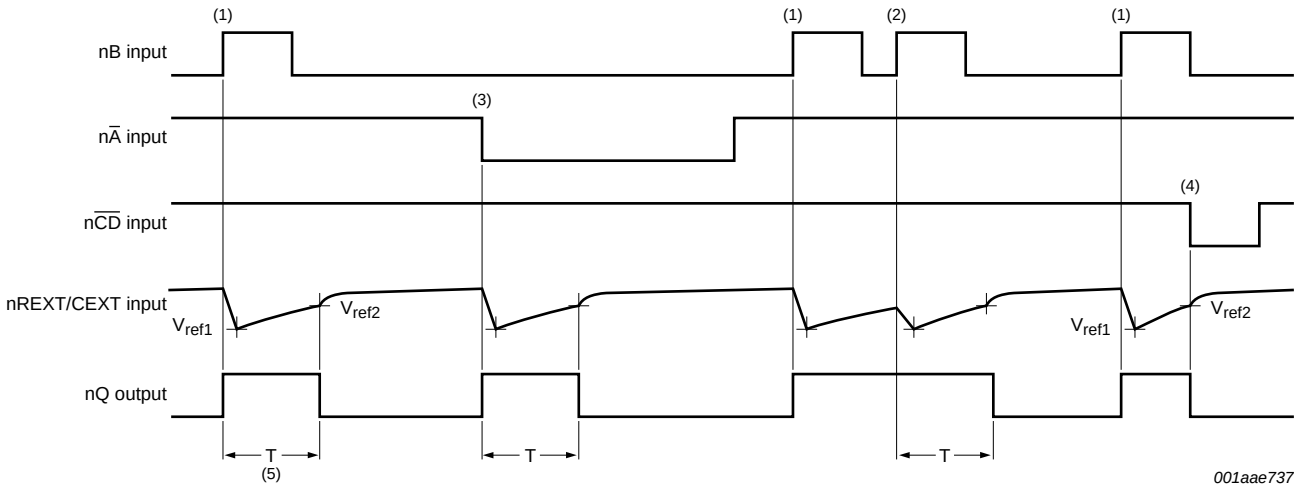
Table 3. Function table

Inputs			Outputs	
nA	**nB**	**nCD**	**nQ**	**nQ**
↓	L	H	⎍	⎍
H	↑	H	⎍	⎍
X	X	L	L	H

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care;
↑ = positive-going transition; ↓ = negative-going transition;

⎍ = one HIGH level output pulse, with the pule width determined by C_{EXT} and R_{EXT};

⎍ = one LOW level output pulse, with the pulse width determined by C_{EXT} and R_{EXT}.



(1) Positive edge triggering.
(2) Positive edge retriggering (pulse lengthening).
(3) Negative edge triggering.
(4) Reset (pulse shortening).
(5) $T = 0.7 \times R_{EXT} \times C_{EXT}$ (see also Figure 6).

Fig 5. Timing diagram

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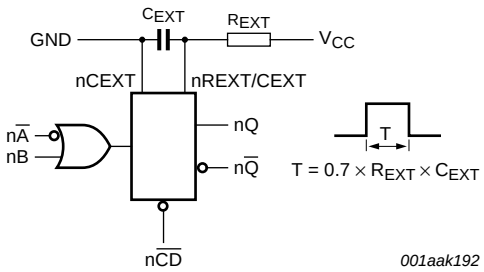


Fig 6. Connection of the external timing components R_{EXT} and C_{EXT}

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			−0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V	[1]	-	±20	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	[1]	-	±20	mA
I_O	output current	$V_O = -0.5$ V to $V_{CC} + 0.5$ V		-	±25	mA
I_{CC}	supply current			-	+50	mA
I_{GND}	ground current			−50	-	mA
T_{stg}	storage temperature			−65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C				
		SO16 package	[2]	-	500	mW
		TSSOP16 package	[3]	-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] P_{tot} derates linearly with 8 mW/K above 70 °C.

[3] P_{tot} derates linearly with 5.5 mW/K above 60 °C.

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8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC4538-Q100			74HCT4538-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		–40	-	+125	–40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V_{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V_{CC} = 6.0 V	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC4538-Q100										
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V_{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V_{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V_{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V_{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = –20 μA; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I_O = –20 μA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –20 μA; V_{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I_O = –4.0 mA; V_{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I_O = –5.2 mA; V_{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = 20 μA; V_{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 4.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I_O = 5.2 mA; V_{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I_I	input leakage current	V_I = V_{CC} or GND; V_{CC} = 6.0 V	-	-	±0.1	-	±1	-	±1	μA
		pin nREXT/CEXT; V_I = 2.0 V or GND; other inputs at V_{CC} or GND; V_{CC} = 6.0 V [1]	-	-	±0.5	-	±5	-	±10	μA

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Table 6. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0$ V	-	-	8.0	-	80	-	160	µA
C_I	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT4538-Q100										
V_{IH}	HIGH-level input voltage	$V_{CC} = 4.5$ V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5$ V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}; $V_{CC} = 4.5$ V								
		$I_O = -20$ µA	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -4.0$ mA	3.98	4.32	-	3.84	-	3.7	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}; $V_{CC} = 4.5$ V								
		$I_O = 20$ µA; $V_{CC} = 4.5$ V	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0$ mA; $V_{CC} = 4.5$ V	-	0.15	0.26	-	0.33	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5$ V	-	-	±0.1	-	±1	-	±1	µA
		pin nREXT/CEXT; $V_I = 2.0$ V or GND; other inputs at V_{CC} or GND; $V_{CC} = 5.5$ V [1]	-	-	±0.5	-	±5	-	±10	µA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	8.0	-	80	-	160	µA
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 2.1$ V; $I_O = 0$ A; other inputs at V_{CC} or GND; $V_{CC} = 4.5$ V to 5.5 V								
		pin $n\overline{A}$, nB	-	50	180	-	225	-	245	µA
		pin $n\overline{CD}$	-	65	234	-	293	-	319	µA
C_I	input capacitance		-	3.5	-	-	-	-	-	pF

[1] This measurement can only be carried out after a trigger pulse is applied.

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10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	Min	Max	
74HC4538-Q100										
t_{PLH}	LOW to HIGH propagation delay	$n\overline{A}$, nB to nQ; see Figure 7								
		V_{CC} = 2.0 V	-	85	265	-	330	-	400	ns
		V_{CC} = 4.5 V	-	31	53	-	66	-	80	ns
		V_{CC} = 5.0 V; C_L = 15 pF	-	27	-	-	-	-	-	ns
		V_{CC} = 6.0 V	-	25	45	-	56	-	68	ns
		$n\overline{CD}$ to $n\overline{Q}$; see Figure 7								
		V_{CC} = 2.0 V	-	83	265	-	340	-	400	ns
		V_{CC} = 4.5 V	-	30	53	-	68	-	80	ns
		V_{CC} = 6.0 V	-	24	45	-	58	-	68	ns
t_{PHL}	HIGH to LOW propagation delay	$n\overline{A}$, nB to $n\overline{Q}$; see Figure 7								
		V_{CC} = 2.0 V	-	83	265	-	330	-	400	ns
		V_{CC} = 4.5 V	-	30	53	-	66	-	80	ns
		V_{CC} = 5.0 V; C_L = 15 pF	-	27	-	-	-	-	-	ns
		V_{CC} = 6.0 V	-	24	45	-	56	-	68	ns
		$n\overline{CD}$ to nQ; see Figure 7								
		V_{CC} = 2.0 V	-	80	265	-	330	-	400	ns
		V_{CC} = 4.5 V	-	29	53	-	66	-	80	ns
		V_{CC} = 6.0 V	-	23	45	-	56	-	68	ns
t_t	transition time	nQ and $n\overline{Q}$; see Figure 7 [2]								
		V_{CC} = 2.0 V	-	19	75	-	95	-	119	ns
		V_{CC} = 4.5 V	-	7	15	-	19	-	22	ns
		V_{CC} = 6.0 V	-	6	13	-	16	-	19	ns

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Table 7. Dynamic characteristics *...continued*

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	Min	Max	
t_W	pulse width	$n\overline{A}$ LOW; see Figure 8								
		V_{CC} = 2.0 V	80	17	-	100	-	120	-	ns
		V_{CC} = 4.5 V	16	6	-	20	-	24	-	ns
		V_{CC} = 6.0 V	14	5	-	17	-	20	-	ns
		nB HIGH; see Figure 8								
		V_{CC} = 2.0 V	80	17	-	100	-	120	-	ns
		V_{CC} = 4.5 V	16	6	-	20	-	24	-	ns
		V_{CC} = 6.0 V	14	5	-	17	-	20	-	ns
		$n\overline{CD}$ LOW; see Figure 8								
		V_{CC} = 2.0 V	80	19	-	100	-	120	-	ns
		V_{CC} = 4.5 V	16	7	-	20	-	24	-	ns
		V_{CC} = 6.0 V	14	6	-	17	-	20	-	ns
		nQ and $n\overline{Q}$ HIGH or LOW; see Figure 8								
		V_{CC} = 5.0 V; C_{EXT} = 0.1 μF; R_{EXT} = 10 kΩ	630	700	770	602	798	595	805	μs
t_{rec}	recovery time	$n\overline{CD}$ to $n\overline{A}$, nB; see Figure 8								
		V_{CC} = 2.0 V	35	6	-	45	-	55	-	ns
		V_{CC} = 4.5 V	7	2	-	9	-	11	-	ns
		V_{CC} = 6.0 V	6	2	-	8	-	9	-	ns
t_{rtrig}	retrigger time	$n\overline{A}$, nB; see Figure 8; $X = C_{EXT} / (4.5 \times V_{CC})$								
		V_{CC} = 2.0 V	-	455 + X	-	-	-	-	-	ns
		V_{CC} = 4.5 V	-	80 + X	-	-	-	-	-	ns
		V_{CC} = 6.0 V	-	55 + X	-	-	-	-	-	ns
R_{EXT}	external resistance	V_{CC} = 2.0 V	10	-	1000	-	-	-	-	kΩ
		V_{CC} = 5.0 V	2	-	1000	-	-	-	-	kΩ
C_{EXT}	external capacitance					no limits				
C_{PD}	power dissipation capacitance	per multivibrator; V_I = GND to V_{CC} [3]	-	136	-	-	-	-	-	pF

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Table 7. Dynamic characteristics *...continued*

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	Min	Max	
74HCT4538-Q100										
t_{PLH}	LOW to HIGH propagation delay	$n\overline{A}$, nB to nQ; see Figure 7								
		V_{CC} = 4.5 V	-	35	60	-	75	-	90	ns
		V_{CC} = 5.0 V; C_L = 15 pF	-	30	-	-	-	-	-	ns
		$n\overline{CD}$ to $n\overline{Q}$; see Figure 7								
		V_{CC} = 4.5 V	-	35	60	-	75	-	90	ns
t_{PHL}	HIGH to LOW propagation delay	$n\overline{A}$, nB to $n\overline{Q}$; see Figure 7								
		V_{CC} = 4.5 V	-	35	60	-	75	-	90	ns
		V_{CC} = 5.0 V; C_L = 15 pF	-	30	-	-	-	-	-	ns
		$n\overline{CD}$ to nQ; see Figure 7								
		V_{CC} = 4.5 V	-	35	60	-	75	-	90	ns
t_t	transition time	nQ and $n\overline{Q}$; see Figure 7 [2]								
		V_{CC} = 4.5 V	-	7	15	-	19	-	21	ns
t_W	pulse width	$n\overline{A}$ LOW; see Figure 8								
		V_{CC} = 4.5 V	20	11	-	25	-	30	-	ns
		nB HIGH; see Figure 8								
		V_{CC} = 4.5 V	16	5	-	20	-	24	-	ns
		$n\overline{CD}$ LOW; see Figure 8								
		V_{CC} = 4.5 V	20	11	-	25	-	30	-	ns
		nQ and $n\overline{Q}$ HIGH or LOW; see Figure 8								
		V_{CC} = 5.0 V; C_{EXT} = 0.1 μF; R_{EXT} = 10 kΩ	630	700	770	602	798	595	805	μs
t_{rec}	recovery time	$n\overline{CD}$ to $n\overline{A}$, nB; see Figure 8								
		V_{CC} = 4.5 V	7	2	-	9	-	11	-	ns
t_{rtrig}	retrigger time	$n\overline{A}$, nB; see Figure 8; X = C_{EXT} / (4.5 × V_{CC})								
		V_{CC} = 4.5 V	-	80 + X	-	-	-	-	-	ns
R_{EXT}	external resistance	V_{CC} = 5.0 V	2	-	1000	-	-	-	-	kΩ
C_{EXT}	external capacitance	V_{CC} = 5.0 V				no limits				

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Table 7. Dynamic characteristics *...continued*

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

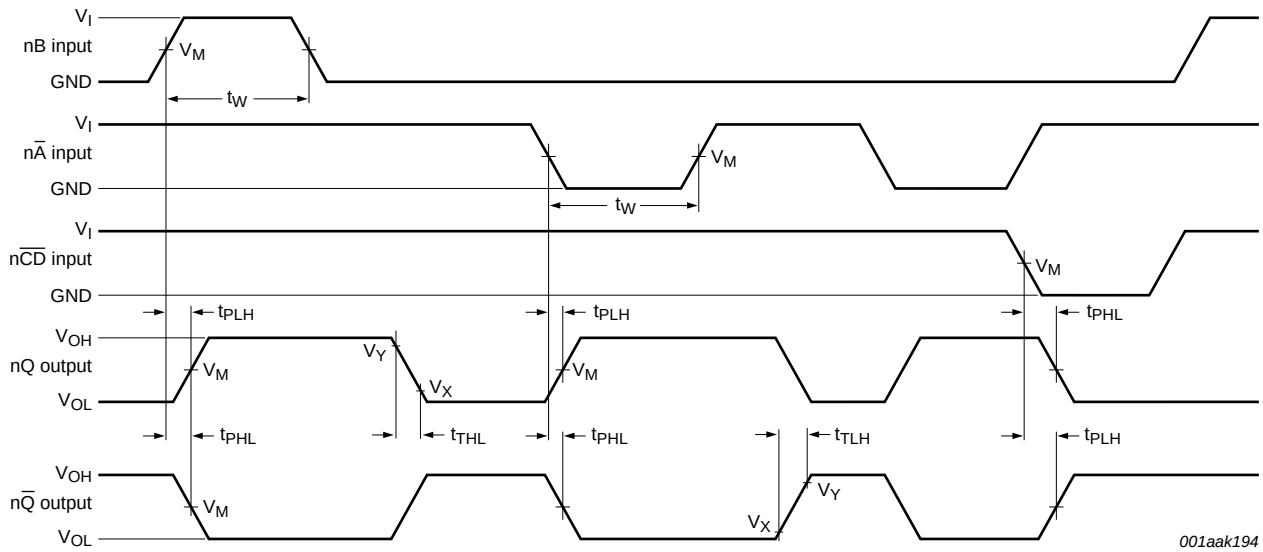
Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	Min	Max	
C_{PD}	power dissipation capacitance	per multivibrator; V_I = GND to (V_{CC} – 1.5 V) [3]	-	138	-	-	-	-	-	pF

[1] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V and V_{CC} = 5.0 V).

[2] t_t is the same as t_{THL} and t_{TLH}.

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times \Sigma(C_L \times V_{CC}^2 \times f_o) + 0.48 \times C_{EXT} \times V_{CC}^2 \times f_o + D \times 0.8 \times V_{CC}$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
D = duty cycle factor in %;
C_{EXT} = external timing capacitance in pF.

11. Waveforms



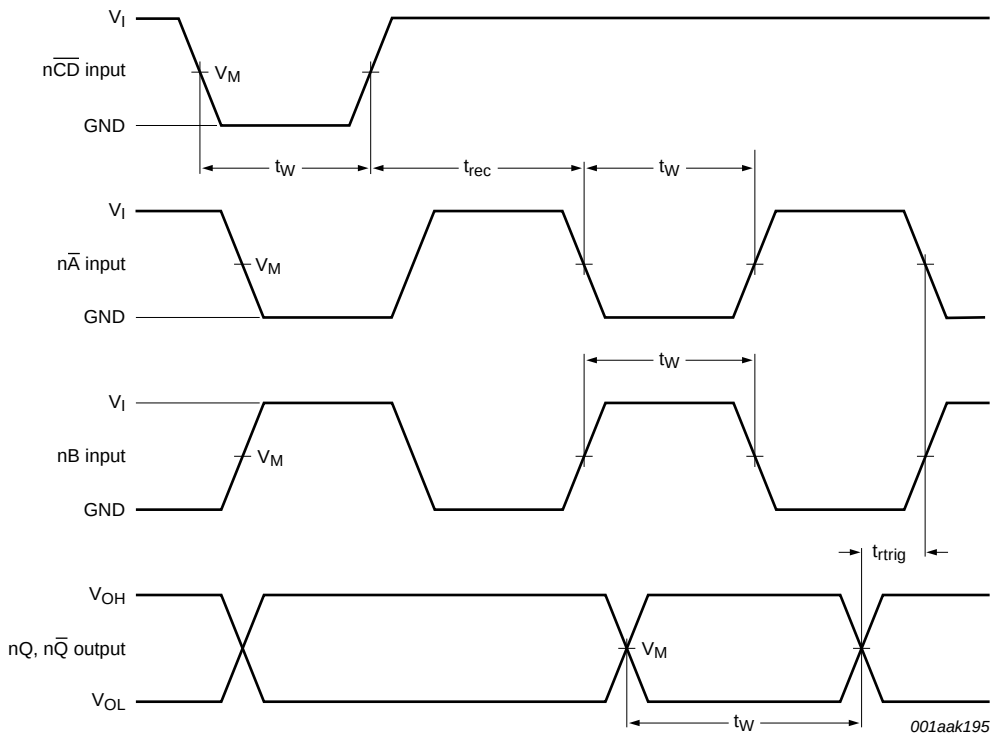
Measurement points are given in Table 8.

Logic levels: V_{OL} and V_{OH} are typical output levels that occur with the output load.

Fig 7. Waveforms showing propagation delays and transition times

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Measurement points are given in Table 8.

Logic levels: V_{OL} and V_{OH} are typical output levels that occur with the output load.

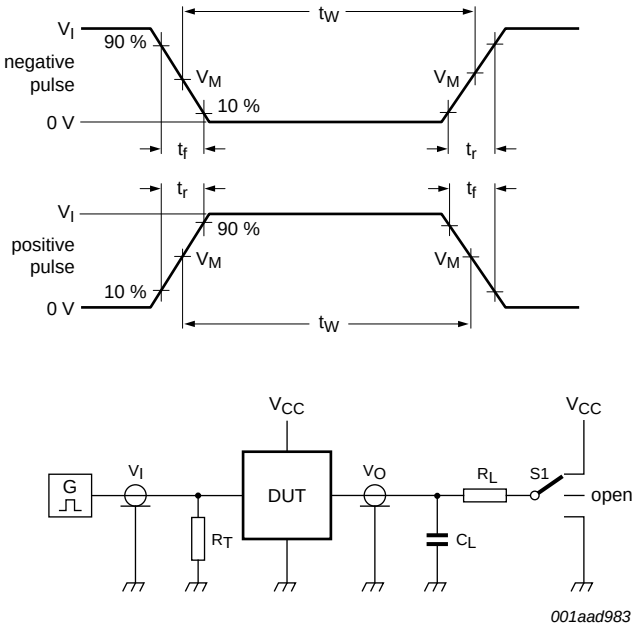
Fig 8. Waveforms showing nA, nB, nQ, nQ pulse widths, recovery and retrigger times

Table 8. Measurement points

Type	Input	Output		
	V_M	V_M	V_X	V_Y
74HC4538-Q100	$0.5V_{CC}$	$0.5V_{CC}$	$0.1V_{CC}$	$0.9V_{CC}$
74HCT4538-Q100	1.3 V	1.3 V	$0.1V_{CC}$	$0.9V_{CC}$

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Test data is given in Table 9.

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch

Fig 9. Test circuit for measuring switching times

Table 9. Test data

Type	Input		Load		S1 position
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}
74HC4538-Q100	V_{CC}	6 ns	15 pF, 50 pF	1 kΩ	open
74HCT4538-Q100	3 V	6 ns	15 pF, 50 pF	1 kΩ	open

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12. Application information

12.1 Power-down considerations

A large capacitor (C_{EXT}) may cause problems when powering-down the monostable due to energy stored in this capacitor. When a system containing this device is powered-down or rapid decrease of V_{CC} to zero occurs, the monostable may sustain damage, due to the capacitor discharging through the input protection diodes. To avoid this possibility, use a damping diode (D_{EXT}) preferably a germanium or Schottky type diode able to withstand large current surges and connect as shown in Figure 10

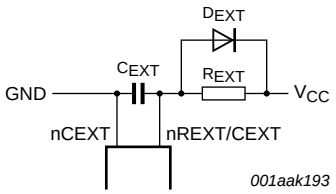
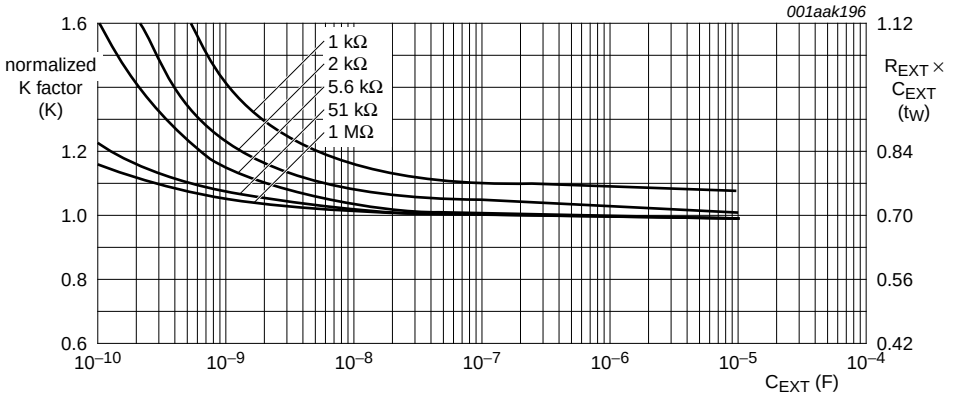


Fig 10. Power-down protection circuit

12.2 Graphs

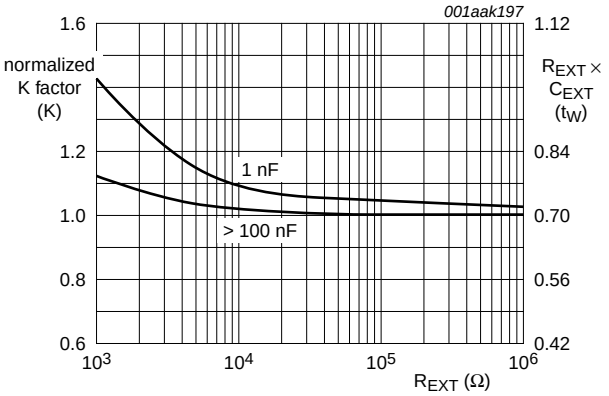


V_{CC} = 4.5 V; T_{amb} = 25 °C.

Fig 11. Typical pulse width accuracy versus external capacitance

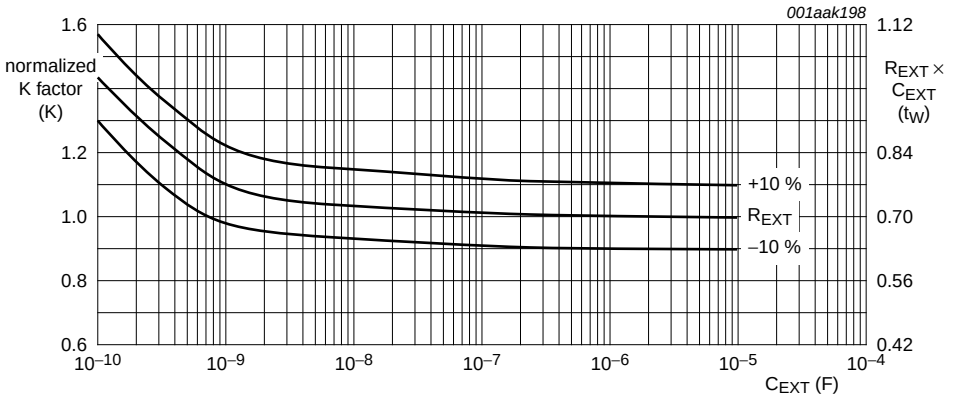
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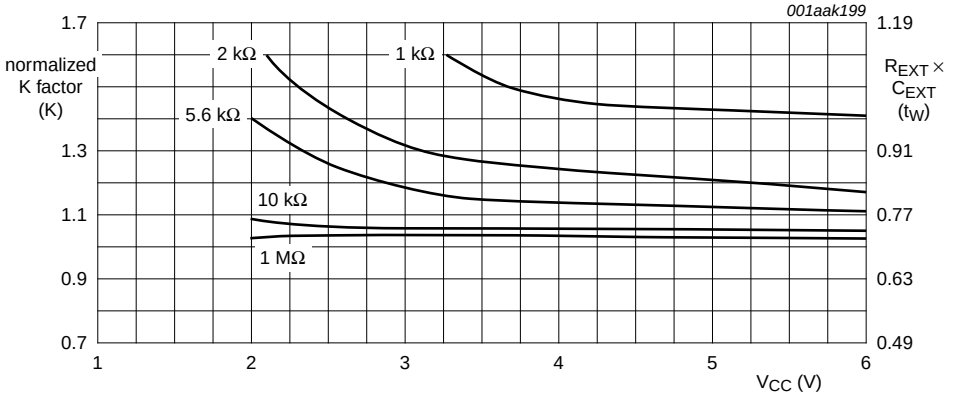
V_{CC} = 4.5 V; T_{amb} = 25 °C.

Fig 12. Typical pulse width accuracy versus external resistance



V_{CC} = 4.5 V; R_{EXT} = 10 kΩ; T_{amb} = 25 °C.

Fig 13. Typical pulse width accuracy versus external capacitance

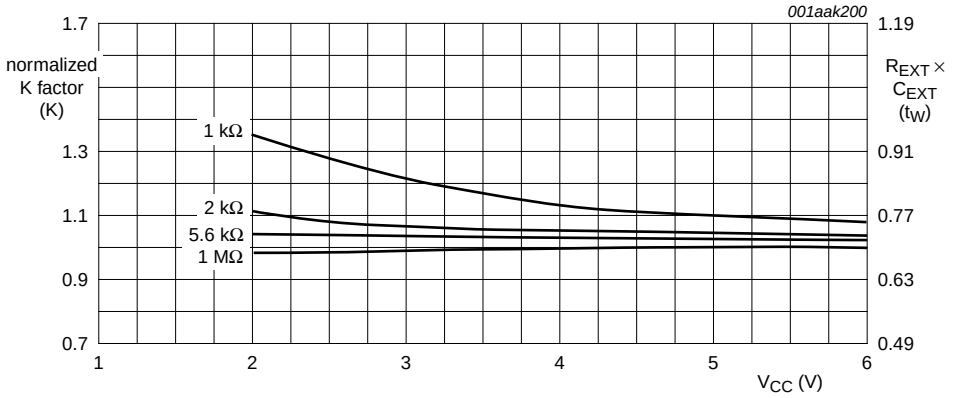


C_{EXT} = 1 nF; T_{amb} = 25 °C.

Fig 14. Typical pulse width accuracy versus power supply

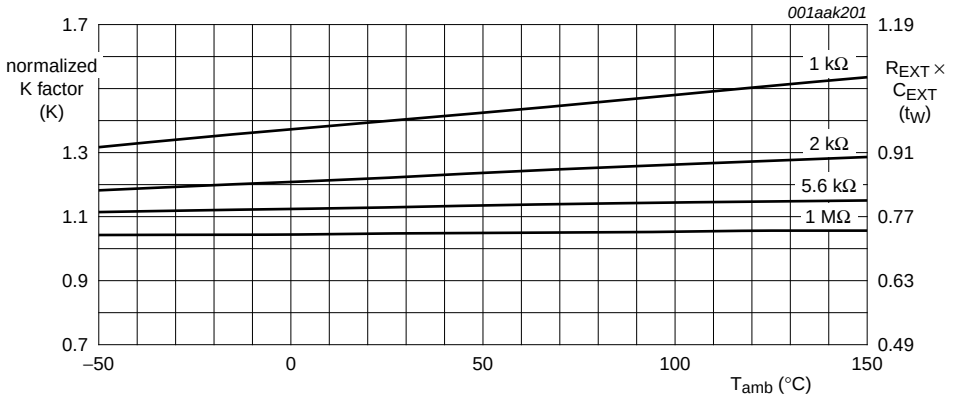
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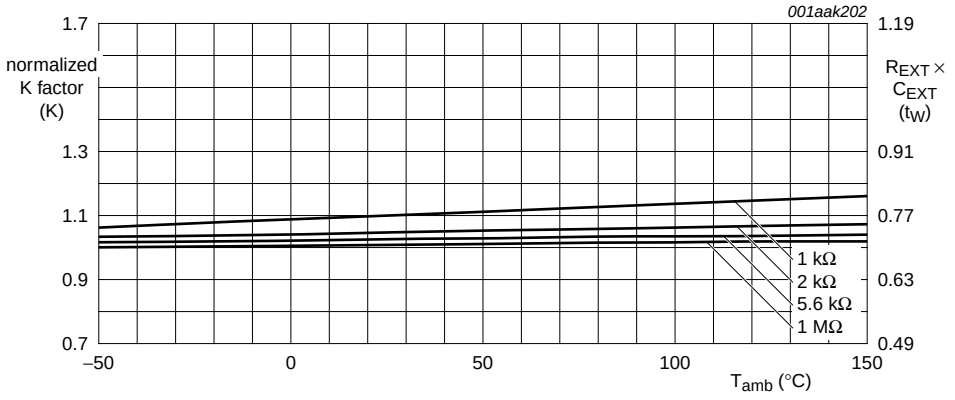
C_{EXT} = 100 nF; T_{amb} = 25 °C.

Fig 15. Typical pulse width accuracy versus power supply



V_{CC} = 4.5 V; C_{EXT} = 1 nF; T_{amb} = 25 °C.

Fig 16. Typical pulse width accuracy versus temperature



V_{CC} = 4.5 V; C_{EXT} = 1 µF; T_{amb} = 25 °C.

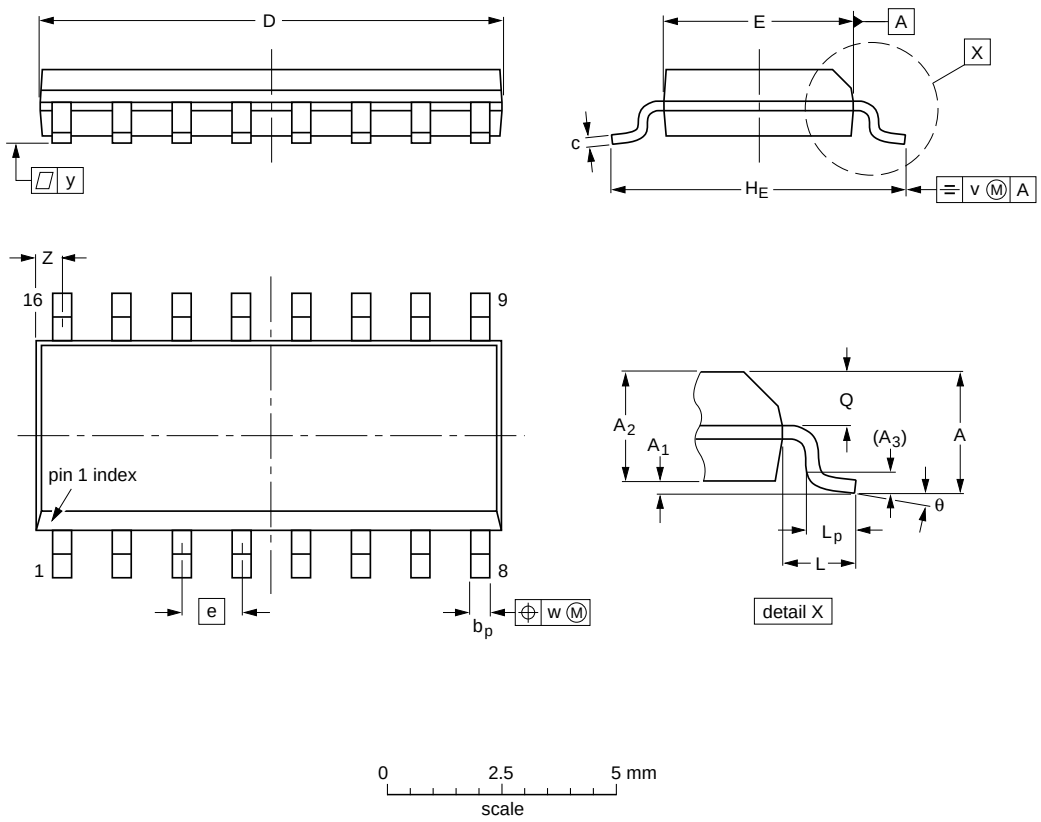
Fig 17. Typical pulse width accuracy versus temperature

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13. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm **SOT109-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8^o 0^o
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

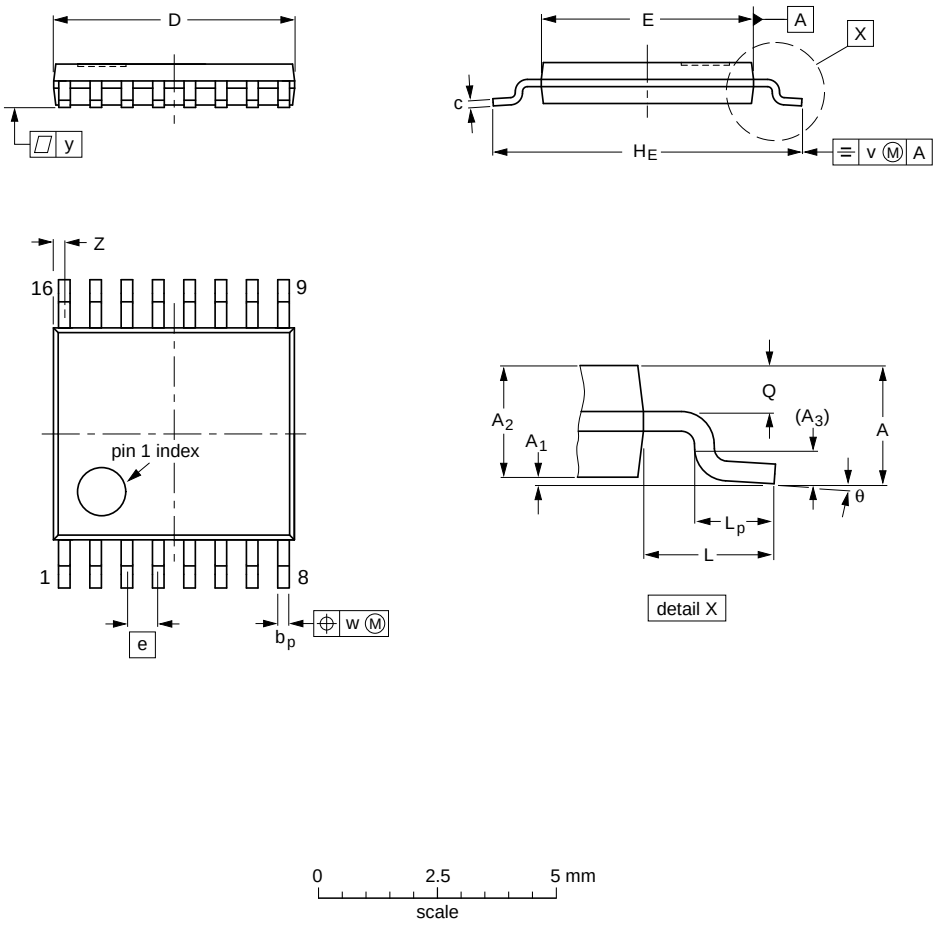
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT109-1	076E07	MS-012				~~99-12-27~~ 03-02-19

Fig 18. Package outline SOT109-1 (SO16)

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TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm **SOT403-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8^o 0^o

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT403-1		MO-153				~~99-12-27~~ 03-02-18

Fig 19. Package outline SOT403-1 (TSSOP16)

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14. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model
TTL	Transistor-Transistor Logic
MIL	Military

15. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT4538_Q100 v.1	20120802	Product data sheet	-	74HC_HCT4538_CNV_2

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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